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AEROSPACE RESEARCH INC BOSTON MASS
INTRINSIC SAFETY REVIEW REPORT.(U)
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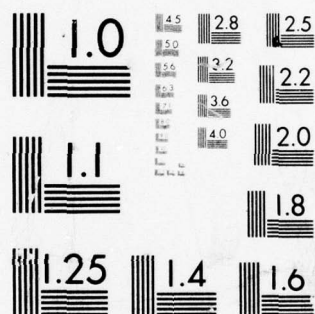
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MICROCOPY RESOLUTION TEST CHART
NATIONAL BUREAU OF STANDARDS-1963-A

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9 TECHNICAL REPORT

6 INTRINSIC SAFETY REVIEW REPORT

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Prepared for:

Department of the Army
U.S. Army Mobility Equipment Research and Development Command
Ft. Belvoir, Virginia 22060

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Contract DAAG53-76-C-0158 new

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Pub No. 575
January 1977

- 1.0 With reference to Paragraph 3.5.2 of the Purchase Description for FIDS Passive Infrared Motion Sensor (PIMS), this report will outline ARI's design as it relates to intrinsic safety in Class 1 hazardous locations. Guidelines were taken from the 1975 edition of NFPA Booklet No. 493. The only part of the PIMS system that is designed for use in a hazardous location is the receiver assembly.
- 2.0 The receiver assembly consists of a mirror assembly which has no electrical power applied and a small printed circuit board that receives +20 VDC from the Signal Processor Card. Typically the receiver draws under 2 ma DC current. In order to ensure adequate system signal to noise ratio it was necessary to have power supply regulation in each head. This necessitated the use of many large value capacitors such that difficulty would be experienced in meeting the requirements of Figure 6-1.5(b) of NFPA 493. It was decided that the only sensible way of meeting the requirement was to coat the P.C. card assembly with heavy coating of high dielectric material. In this configuration, the only place a short circuit could possibly cause an arc would be at the terminal strip located inside the plastic and metal cover assembly. Reference to the schematic diagram shows the circuit configuration. A diagram is also included showing the component layout.
- 2.1 Pin 5 (tamper) was designed to detect shorts to +20V or ground. There is normally under +1 VDC at this point and it is current limited by over 5K ohms.
- Pin 2 (RCVR output) has a 330 ohm resistor in series with the signal output. If pin 2 were shorted to ground and the output of the op-amp was at +16 V (normally +8V) the maximum current would be 12 ma (as per spec. of A776). Additional protection is provided by the 330 ohm resistor (which also isolates coax capacitance). Extrapolating the curves of Figure 6 - 1.5(b) of NFPA Booklet No. 493 shows that (C+330 ohm) would result in ignition voltage of over 50v. Dividing by two as per section 6 - 2.1 of No. 493 gives 25V, which is above the worst case voltage of +16.
- Copy Shurt R78-0271*
- A*

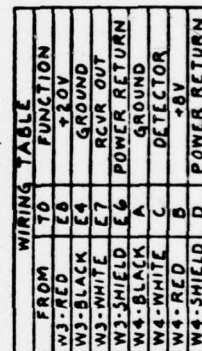
2.2

If pin 5 (+20V to Head) were shorted to ground at the receiver terminal strip the following situations (a through e) would occur.

- a) For FIDS, the 10V to 20V, DC to DC converter on the signal processor card limits itself to 75 ma. (Not used on J-SIIDS).
- b) In series with the (+20V to Head) line are two 150 ohm, 2 watt resistors in parallel, or 75 ohms. Extrapolating the curve in NFPA No. 493 for a 47 uf capacitor with 75 ohms in series gives a voltage of approximately 40V. Dividing this by two as per 6 - 2.1 of NFPA No. 493 gives $\pm 20V$. 75 ohms would limit the current to under 300 ma (if there were no intrinsic safety barrier).
- c) It is ARI's understanding that the power fed to the PIMS processor card will be done so in an intrinsically safe manner. There will be no barrier between the processor and any of its receivers. Suitable current limiting would be as follows. During FIDS operation, the nominal current draw is 5 ma for the processor card and 1.5 ma per receiver (MAX. 6 receivers). Total FIDS current is normally 14 ma. In J-SIIDS operation an additional 12 ma is required to drive the two relays in the adaptor box. Total J-SIIDS current therefore is 26 ma (typical). It is suggested that the power supply be limited (or fused) at around 100 ma. That level would suffice for FIDS operation also. In addition to preventing ignition at the receivers, a current limiter set to 100 ma would prevent damage to the signal processor card if exposed to any induced or random failures and short circuits.
- d) Another safety feature, for J-SIIDS only, is the IN4004 diode which is located in the adaptor box. This diode is in series with the +20V to the processor card. The forward resistance will act like a current limiter in conjunction with the intrinsic safety limiter and the two 150 ohm resistors. Without intrinsic safety limiting it would act as a fuse because over 200 ma would flow under short circuit conditions discussed in (b), which is sufficient to destroy the junction.

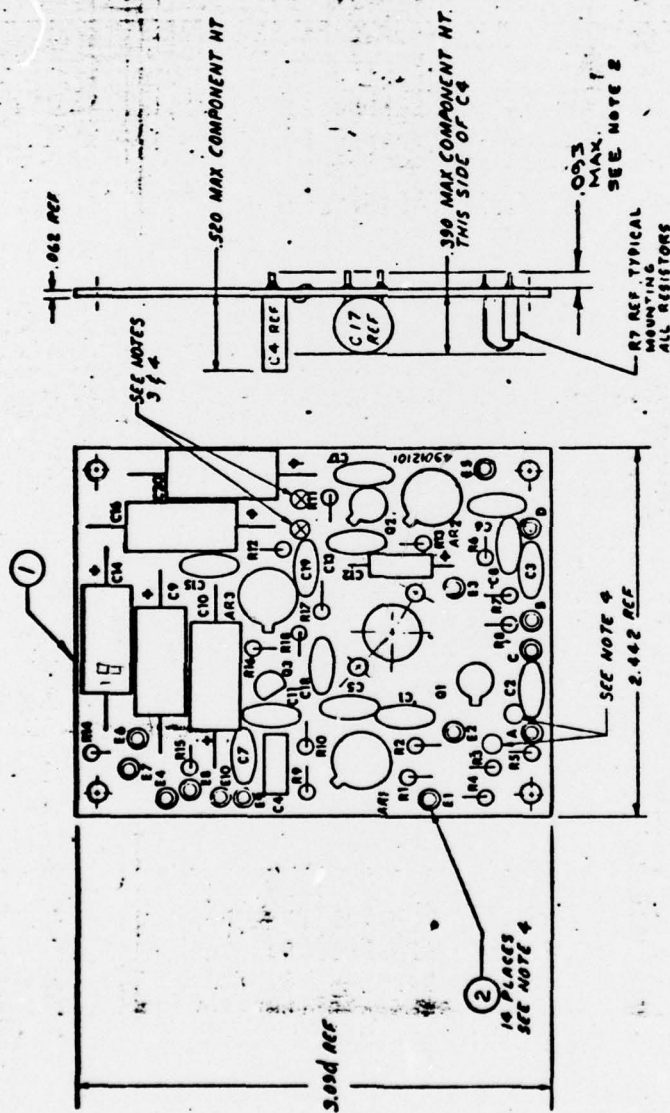
e) At the input to each head on the +20V line is a 100 ohm series resistor and then a 47 uf capacitor to ground. The composite R/C combination is similar to section (b); i.e., safe to run at +20V.

2.3 The connections to the PC card from the thermistor detector is a high impedance with insufficient capacity in the circuit to cause ignition.



REF	QTY	DESCRIPTION
6	430-3101	SCHEMATIC-RECEIVER
5	67606003	TIE-CABLE
4	2	SCREW,CAP 2-56 X 1/2
3	1	CABLE ASSEMBLY
2	430-2102	DETECTOR HOUSING ASSEMBLY
1	430-2101	P.C. ASSEMBLY RECEIVER
QTY	1	RECEIVER

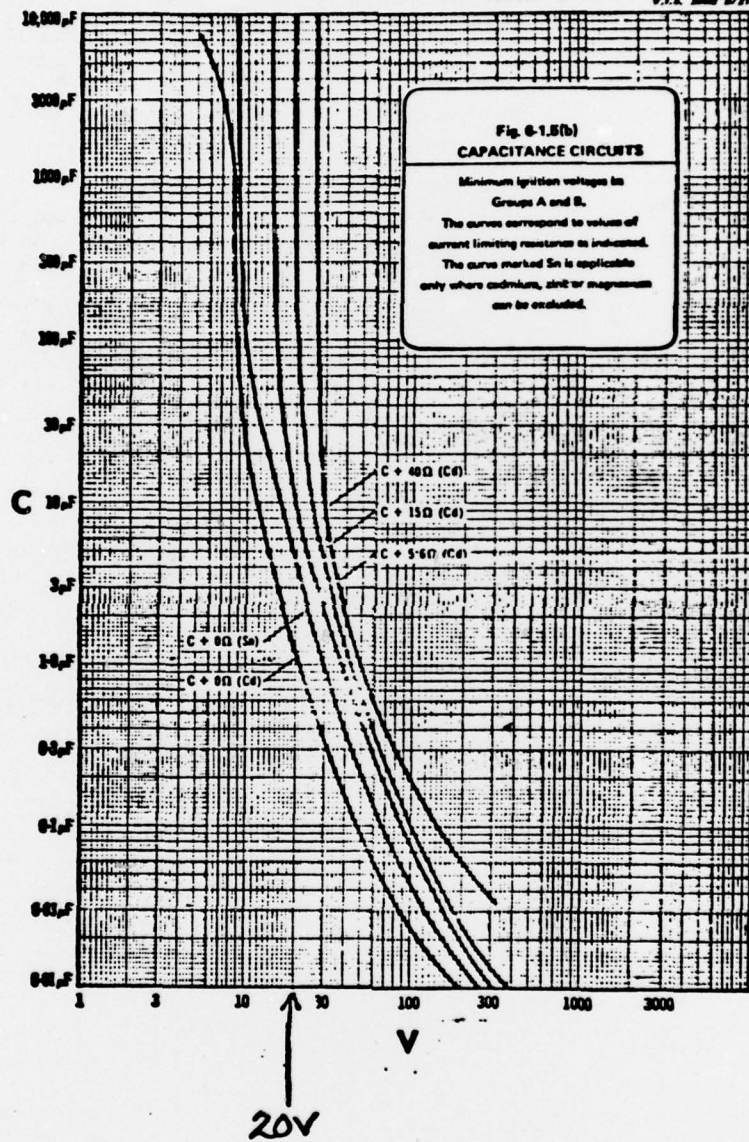
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- NOTES.
1. ASSEMBLE AS SHOWN FOR COMPLETE COMPONENT DESCRIPTION SEE PL 490-2101
 2. CUT ALL COMPONENT LEAD TO DIMENSIONS SHOWN
 3. INDICATES INTERFACIAL CONNECTION (STITCH)
 4. AFTER ASSEMBLY, CALIBRATION AND FINAL TEST, MASK TERMINALS A, B, C, D, E, I THRU E10 AND BOTH SIDES OF 9 PAD AREAS NOTED. THEN APPLY A 5 MIL COATING OF ITEM 5 (CONAP CE-1132) PER PROCESS SPECIFICATION 490-4100.

SEE PARTS LIST 490-2101

REV	DATE	BY	CHKD	APP'D	DESCRIPTION
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6-2 Maximum Voltage and Current Levels.

6-2.1 Maximum voltage and current levels in intrinsically safe circuits approved without ignition testing shall not exceed 50 percent of the current determined from Figures 6-1.3(a), 6-1.3(b) and 6-1.4(a) through 6-1.4(d), or of the voltage determined from Figures 6-1.5(a) and 6-1.5(b) for given circuit constants. Higher voltage and current levels shall be permissible if their safety is demonstrated by test.

6-2.2 Circuit Conditions. The circuit conditions shall include all normal and fault conditions described in this standard.

6-3 Temperature Classification. An assessment or test shall be carried out to establish the operating temperature marking per *National Electrical Code* 500-2 (c).

6-4 Voltage Test Methods. The voltage tests shall be as described in Section 5-8.

CONAP INC.

CONTROLLED MATERIALS APPLICATIONS

PLANNED PROGRESS THROUGH
POLYMER RESEARCH**TECHNICAL INFORMATION**SINGLE COMPONENT
COATING FOR
PRINTED CIRCUITS

CONAP, INC. 1405 BUFFALO STREET • OLEAN, NEW YORK 14760 • PHONE (716) 372-9650
CONAP (CANADA) LTD. 5200 DIXIE RD. • AEROWOOD INDUSTRIAL PLAZA • MISSISSAUGA, ONTARIO, CANADA • TWX: 510-245-2769
CONAP CE-1132 • PHONE (416) 625-2520

CONAP CE-1132 is a single component liquid coating for printed circuits, and is a stabilized synthetic polymer. It has been formulated specifically to protect assemblies against environmental conditions such as contamination and high humidity; and at the same time, ruggedize the unit against shock and vibration. In addition, CONAP CE-1132 offers an ease of handling seldom found in similar coatings; i.e., it can be applied by spray, brush or dip; there is little runoff and cure cycles are short.

PROTECTION 'PLUS' FOR PRINTED CIRCUITS**CE-1132 COMBINES:**

- EXTRA-LONG DIP TANK STABILITY • EASE OF REPAIR • ECONOMY
- FAST-LOW TEMPERATURE CURE • EXCELLENT HUMIDITY RESISTANCE
- GOOD ELECTRICAL PROPERTIES • UNIFORM COATING THICKNESS

CONAP CE-1132 is also easily repairable. Components can be placed and replaced in coated areas, using ordinary repair procedures, without danger of carbonization at 175°C, or interference with the making of sound solder joints.

And to make field repair easier, especially where ovens are not available, CONAP CE-1133 has been developed so that it will cure at room temperature. This is supplied in kit form, each kit containing CE-1133, a brush and CONAP S-8 Solvent.

A tracer dye is used in CE-1132 and CE-1133 to aid in inspection of the cured film under 'black' light.

PRODUCT SPECIFICATIONS

Brookfield Viscosity @ 25°C.....	500 - 800
Specific Gravity @ 25°C.....	0.97 - 1.01
Solids Content, %.....	30 - 33
Flashpoint, °F, Tag Closed Cup.....	55
Dip Tank Stability.....	Indefinite *

- * Although after a matter of days, due to solvent evaporation, there may be some increase in viscosity. This may be corrected with CONAP S-8 Solvent.

TYPICAL PROPERTIES OF CURED FILM

The properties of CE-1132 films presented in this bulletin were obtained on samples prepared in the laboratory. The values are average, based on several tests and are not intended for use in preparation of specifications.

Physical Properties

Color.....	Clear
Hardness, Shore D.....	80
Water Absorption, %, 24 hr. Immersion.....	0.18
Chemical and Solvent Resistance.....	Fair to Good*
Fungus Resistance.....	Non-Nutrient (MIL-E-5272C)
Flexibility, Bend over 1/8" Mandrel.....	No cracking or crazing of coating
Repairability, Soldering Iron.....	Excellent
Thermal Shock, 5 cycles from -55°C to 95°C.....	Passes
Inspection.....	Invisible dye, fluorescent under black light

- * If it becomes necessary to remove the coating from the entire assembly, this feature enables the user to remove the cured film quite easily by using methyl ethyl ketone. Care should be exercised in the removal of the coating in that if the assembly is exposed to this solvent for too long a period, it or any attached components may also be attacked.

Before recoating the assembly, it is recommended that the assembly be recleaned and thoroughly dried.

Electrical Properties

	25°C	60°C
Dielectric Strength, vpm		
1 Mil film.....	6500	-
3 Mil film.....	4000	-
Dielectric Constant 100Hz.....	3.35	3.50
1KHz.....	3.30	3.45
1MHz.....	3.40	-
Dissipation Factor 100Hz.....	.007	.007
1KHz.....	.007	.007
1MHz.....	.006 ¹⁵	-
Volume Resistivity, ohm-cm.....	1.4x10 ¹⁵	
Insulation Resistance, ohms (4 mil films)*		
Initial (at 25°C - 50% R.H.).....	2.50x10 ¹³	
After 1 day (at 65°C - 95% R.H.).....	2.40x10 ¹²	
After 7 days (at 65°C - 95% R.H.).....	3.50x10 ¹⁰	
After 10 days (at 65°C - 95% R.H.).....	2.10x10 ¹⁰	
After conditioning 24 hours @ 25°C - 50% R.H.....	5.70x10 ¹⁰	
Dielectric Withstanding Voltage, 1500 v.a.c.*.....	No flashover or breakdown	

* Tested in accordance with MIL-I-46058. The films maintained excellent adhesion to the epoxy-glass laminates during the 10-day humidity/temperature cycling test. No underfilm corrosion of the copper conductors was observed.

APPLICATION INFORMATION

CONAP CE-1132 does not require continuous mixing; nor is deairation necessary. Air bubbles generated by pouring will normally dissipate within a few minutes.

CONAP CE-1132 is a high performance printed circuit coating and the ultimate performance of the cured coating is dependent on process controls used in application of the coating. Cleanliness of the substrate is a major factor in preventing underfilm corrosion. Boards MUST be clean, oil-free and dry. For specific recommendations, please request Technical Bulletin C-115.

Conventional dipping, spraying or brushing techniques may be used to apply CE-1132. It is recommended that the coating be used as supplied for dip coating. A single dip coat on a board will deposit a film thickness of 2 to 2 1/2 mils, if the withdrawal rate is 4 inches per minute.

CE-1132 may be sprayed by dilution with CONAP S-8 Solvent.

Two coats are recommended for optimum performance. However, one coat may perform well for non-critical applications. Cure is accomplished by pre-baking 15 minutes at 50°C for each coating application followed by a final cure of 60 minutes at 75°C.

For optimum protection against severe humidity, allow a 30 minute air dry after each coat and pre-bake 30 minutes at 50°C, followed by a FINAL CURE of 4 hours at 75°C.

HANDLING AND STORAGE

Maintain containers at room temperature and keep securely closed when not in use to prevent solvent evaporation.

CONAP CE-1132 has a shelf life of at least 1 year when stored in original, unopened containers.

CAUTION: CE-1132 contains solvents and should be handled in the same manner as any material containing solvents. Avoid skin contact with uncured materials and inhalation of vapors. If contact does occur, wash with soap and water.

AVAILABILITY

CONAP CE-1132 is available in quart, gallon, 5-gallon, and drum containers.

An Evaluation Kit, containing 1 quart of CE-1132, 1 pint of CE-1133 and 1 pint of CONAP S-8 Solvent, is available for \$10.00 per kit.

P.O.B. Olean, New York 14760
Mississauga, Ontario, Canada

TERMS: Net 30 Days

μA776

MULTI-PURPOSE PROGRAMMABLE OPERATIONAL AMPLIFIER

FAIRCHILD LINEAR INTEGRATED CIRCUIT

DESCRIPTION — The μA776 Programmable Operational Amplifier is constructed using the Fairchild Planar[®] epitaxial process. High input impedance, low supply currents, and low input noise over a wide range of operating supply voltages coupled with programmable electrical characteristics result in an extremely versatile amplifier for use in high accuracy, low power consumption analog applications. Input noise voltage and current, power consumption, and input current can be optimized by a single resistor or current source that sets the chip quiescent current for nano-watt power consumption or for characteristics similar to the μA741. Internal frequency compensation, absence of latch up, high slew rate and short circuit current protection assure ease of use in long time integrators, active filters, and sample and hold circuits.

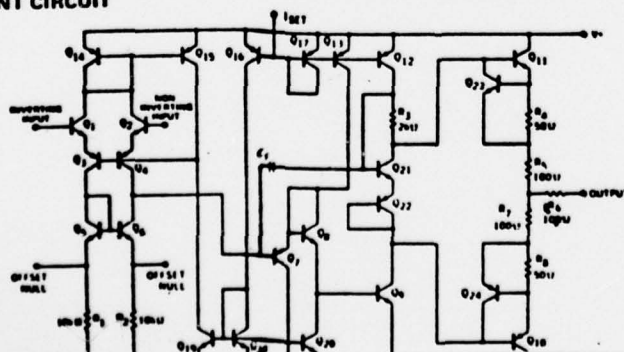
- MICROPOWER CONSUMPTION
- $\pm 1.2\text{V}$ to $\pm 18\text{V}$ OPERATION
- NO FREQUENCY COMPENSATION REQUIRED
- LOW INPUT BIAS CURRENTS
- WIDE PROGRAMMING RANGE

- HIGH SLEW RATE
- LOW NOISE
- SHORT CIRCUIT PROTECTION
- OFFSET NULL CAPABILITY
- NO LATCH UP

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	$\pm 18\text{V}$
Internal Power Dissipation (Note 1)	
Metal Can	500 mW
DIP	670 mW
Mini DIP	310 mW
Differential Input Voltage	$\pm 30\text{V}$
Input Voltage (Note 2)	$\pm 15\text{V}$
Voltage Between Offset Null and V_-	$\pm 0.5\text{V}$
I_{SET} (Maximum Current at I_{SET})	500 μA
V_{SET} (Maximum Voltage to Ground at I_{SET})	$(V_+ - 2.0\text{V}) < V_{SET} < V_+$
Storage Temperature Range	
Metal Can, DIP	-65°C to $+150^\circ\text{C}$
Mini DIP	-55°C to $+125^\circ\text{C}$
Operating Temperature Range	
Military (776)	-55°C to $+125^\circ\text{C}$
Commercial (776C)	0°C to $+70^\circ\text{C}$
Lead Temperature (Soldering, 60 seconds)	
Metal Can, DIP	300°C
Mini DIP	260°C
Output Short-Circuit Duration (Note 3)	Indefinite

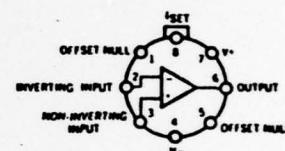
EQUIVALENT CIRCUIT



CONNECTION DIAGRAMS

8-LEAD METAL CAN (TOP VIEW)

PACKAGE OUTLINE 5B



ORDER INFORMATION

TYPE	PART NO.
776	776HM
776C	776MC

14-LEAD DIP (TOP VIEW)

PACKAGE OUTLINE 6A

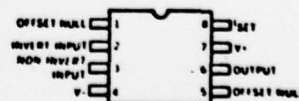


ORDER INFORMATION

TYPE	PART NO.
776	776DM
776C	776DC

8-LEAD MINI DIP (TOP VIEW)

PACKAGE OUTLINE 9T



ORDER INFORMATION

TYPE	PART NO.
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FAIRCHILD LINEAR INTEGRATED CIRCUITS • μ A776

± 15 VOLT OPERATION FOR 776

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Specified)

PARAMETERS	CONDITIONS	$I_{SET} = 1.5\mu\text{A}$			$I_{SET} = 15\mu\text{A}$			UNITS
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input Offset Voltage	$R_S < 10\text{k}\Omega$		2.0	5.0		2.0	5.0	mV
Input Offset Current	$R_S < 10\text{k}\Omega$		0.7	3.0		2.0	15	nA
Input Bias Current			2.0	7.5		15	50	nA
Input Resistance			50			5.0		M Ω
Input Capacitance			2.0			2.0		pF
Offset Voltage Adjustment Range			9.0			18		mV
Large Signal Voltage Gain	$R_L > 75\text{k}\Omega$, $V_{OUT} = \pm 10\text{V}$	200k	400k					V/V
	$R_L > 5\text{k}\Omega$, $V_{OUT} = \pm 10\text{V}$				100k	400k		V/V
Output Resistance			5.0k			1.0k		Ω
Output Short-Circuit Current			3.0			12		mA
Supply Current			20	25		160	180	μA
Power Consumption				0.75			5.4	mW
Transient Response (unity gain)	Risetime	$V_{IN} = 20\text{mV}$, $R_L > 5\text{k}\Omega$, $C_L = 100\text{pF}$		1.6		0.35		μs
	Overshoot			0		10		%
Slew Rate	$R_L > 5\text{k}\Omega$		0.1			0.8		V/ μs
Output Voltage Swing	$R_L > 75\text{k}\Omega$	± 12	± 14					V
	$R_L > 5\text{k}\Omega$				± 10	± 13		V

The following specifications apply $-55^\circ\text{C} < T_A < +125^\circ\text{C}$

Input Offset Voltage	$R_S < 10\text{k}\Omega$	6.0	6.0	mV
Input Offset Current	$T_A = +125^\circ\text{C}$	5.0	15	nA
	$T_A = -55^\circ\text{C}$	10	40	nA
Input Bias Current	$T_A = +125^\circ\text{C}$	7.5	50	nA
	$T_A = -55^\circ\text{C}$	20	120	nA
Input Voltage Range		± 10	± 10	V
Common Mode Rejection Ratio	$R_S < 10\text{k}\Omega$	70 90	70 90	dB
Supply Voltage Rejection Ratio	$R_S < 10\text{k}\Omega$	25 150	25 150	$\mu\text{V/V}$
Large Signal Voltage Gain	$R_L > 75\text{k}\Omega$, $V_{OUT} = \pm 10\text{V}$	100k	75k	V/V
Output Voltage Swing	$R_L > 75\text{k}\Omega$	± 10	± 10	V
Supply Current		30	200	μA
Power Consumption		0.9	6.0	mW

FAIRCHILD LINEAR INTEGRATED CIRCUITS • μ A776

± 13 VOLT OPERATION FOR 776

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Specified)

PARAMETERS	CONDITIONS	$I_{SET} = 1.5\mu\text{A}$			$I_{SET} = 15\mu\text{A}$			UNITS
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input Offset Voltage	$R_S < 10\text{k}\Omega$		2.0	5.0		2.0	5.0	mV
Input Offset Current			0.7	3.0		2.0	15	nA
Input Bias Current			2.0	7.5		15	50	nA
Input Resistance			50			5.0		M Ω
Input Capacitance			2.0			2.0		pF
Offset Voltage Adjustment Range			9.0			18		mV
Large Signal Voltage Gain	$R_L > 75\text{k}\Omega$, $V_{OUT} = \pm 1\text{V}$	50k	200k					V/V
	$R_L > 5\text{k}\Omega$, $V_{OUT} = \pm 1\text{V}$				50k	200k		V/V
Output Resistance			5k			1k		Ω
Output Short-Circuit Current			3.0			5.0		mA
Supply Current			13	20		130	160	μA
Power Consumption			78	120		780	960	μW
Transient Response (unity gain)	Risetime	$V_{IN} = 20\text{mV}$, $R_L > 5\text{k}\Omega$, $C_L < 100\text{pF}$						μs
	Overshoot							%
Slew Rate	$R_L > 5\text{k}\Omega$		0.03			0.35		V/ μs
The following specifications apply for $-55^\circ\text{C} < T_A < +125^\circ\text{C}$								
Input Offset Voltage	$R_S < 10\text{k}\Omega$			6.0			6.0	mV
Input Offset Current	$T_A = +125^\circ\text{C}$			5.0			15	nA
	$T_A = -55^\circ\text{C}$			10			40	nA
Input Bias Current	$T_A = +125^\circ\text{C}$			7.5			50	nA
	$T_A = -55^\circ\text{C}$			20			120	nA
Input Voltage Range		± 1.0			± 1.0			V
Common Mode Rejection Ratio	$R_S < 10\text{k}\Omega$	70	86		70	86		dB
Supply Voltage Rejection Ratio	$R_S < 10\text{k}\Omega$		25	150		25	150	$\mu\text{V/V}$
Large Signal Voltage Gain	$R_L > 75\text{k}\Omega$, $V_{OUT} = \pm 1\text{V}$	25k						V/V
	$R_L > 5\text{k}\Omega$, $V_{OUT} = \pm 1\text{V}$				25k			V/V
Output Voltage Swing	$R_L > 75\text{k}\Omega$	± 2.0	± 2.4					V
	$R_L > 5\text{k}\Omega$				± 1.9	± 2.1		V
Supply Current			25			180		μA
Power Consumption			150			1080		μW

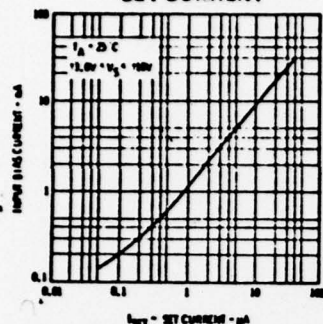
NOTES

1. Rating applies to ambient temperatures up to 70°C . Above 70°C ambient derate linearly at $6.3\text{ mW}/^\circ\text{C}$ for Metal Can, $8.3\text{ mW}/^\circ\text{C}$ for the DIP, and $5.6\text{ mW}/^\circ\text{C}$ for the Mini DIP.
2. For supply voltages less than $\pm 15\text{ V}$, the absolute maximum input voltage is equal to the supply voltage.
3. Short Circuit may be to ground or either supply. Rating applies to $+125^\circ\text{C}$ case temperature or $+75^\circ\text{C}$ ambient temperature for $I_{SET} < 30\mu\text{A}$.

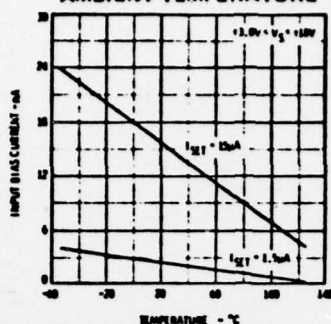
FAIRCHILD LINEAR INTEGRATED CIRCUITS • $\mu A776$

TYPICAL PERFORMANCE CURVES FOR 776 AND 776C

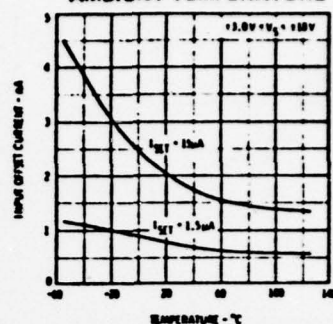
**INPUT BIAS CURRENT
AS A FUNCTION OF
SET CURRENT**



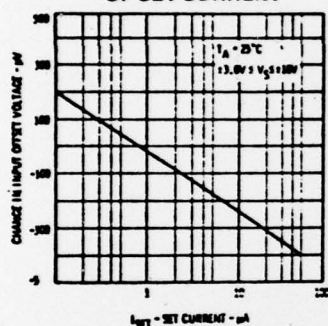
**INPUT BIAS CURRENT
AS A FUNCTION OF
AMBIENT TEMPERATURE**



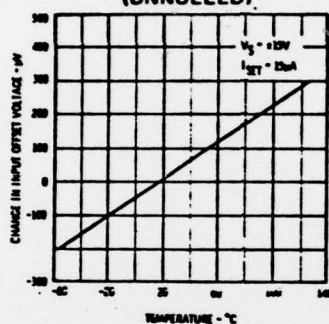
**INPUT OFFSET CURRENT
AS A FUNCTION OF
AMBIENT TEMPERATURE**



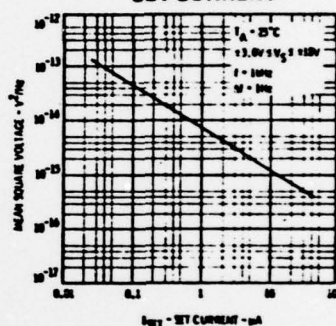
**CHANGE IN INPUT OFFSET
VOLTAGE AS A FUNCTION
OF SET CURRENT**



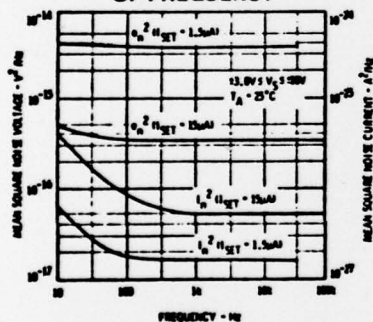
**CHANGE IN INPUT OFFSET
VOLTAGE AS A FUNCTION
OF AMBIENT TEMPERATURE
(UNNULL)**



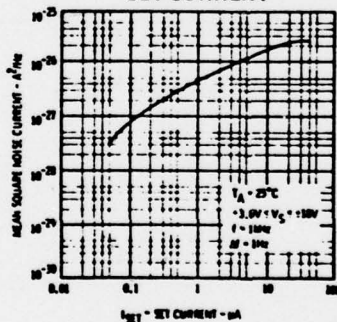
**INPUT NOISE VOLTAGE
AS A FUNCTION OF
SET CURRENT**



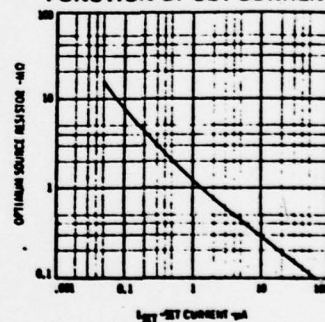
**INPUT NOISE VOLTAGE AND
CURRENT AS A FUNCTION
OF FREQUENCY**



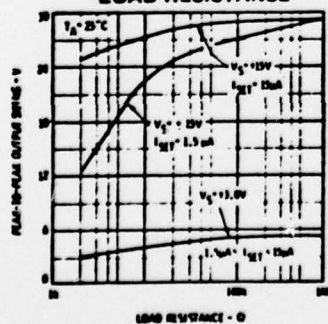
**INPUT NOISE CURRENT
AS A FUNCTION OF
SET CURRENT**



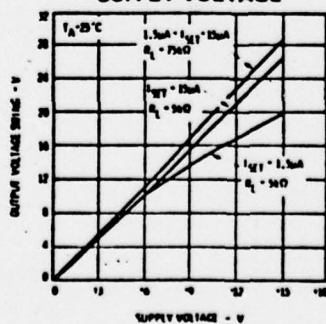
**OPTIMUM SOURCE RESISTOR
FOR MINIMUM NOISE AS A
FUNCTION OF SET CURRENT**



**OUTPUT VOLTAGE SWING
AS A FUNCTION OF
LOAD RESISTANCE**



**OUTPUT VOLTAGE SWING
AS A FUNCTION OF
SUPPLY VOLTAGE**



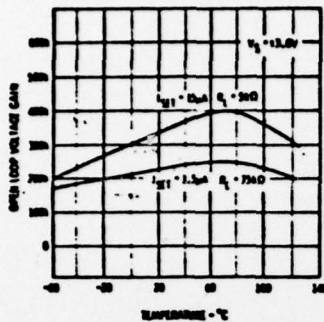
**GAIN-BANDWIDTH
PRODUCT AS A FUNCTION
OF SET CURRENT**



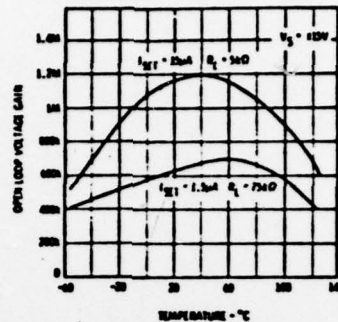
FAIRCHILD LINEAR INTEGRATED CIRCUITS • $\mu A776$

TYPICAL PERFORMANCE CURVES FOR 776 AND 776C

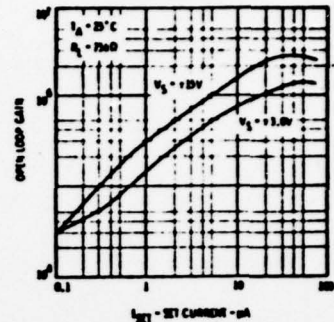
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF AMBIENT TEMPERATURE



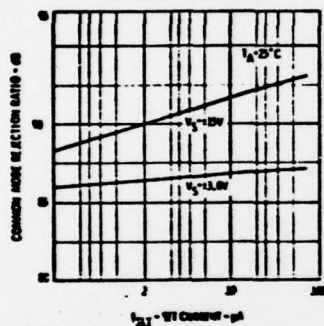
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF AMBIENT TEMPERATURE



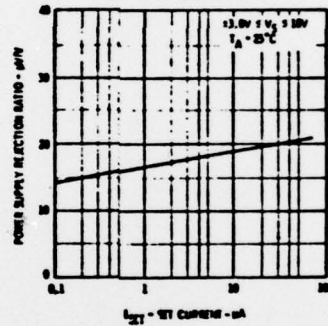
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SET CURRENT



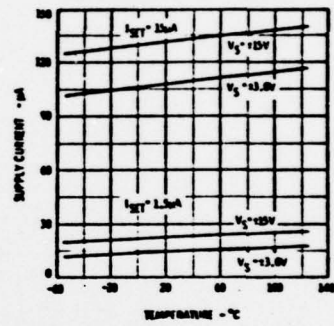
COMMON MODE REJECTION RATIO AS A FUNCTION OF SET CURRENT



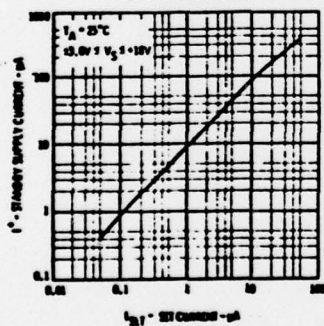
POWER SUPPLY REJECTION RATIO AS A FUNCTION OF SET CURRENT



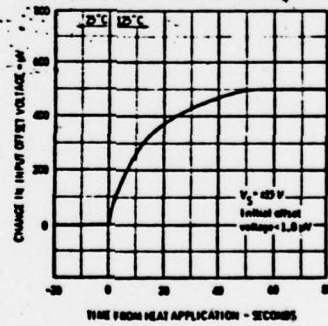
SUPPLY CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



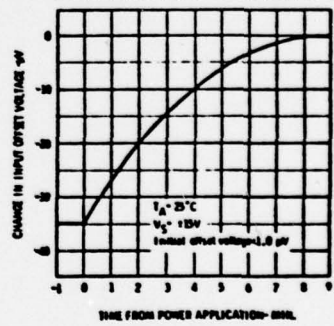
STANDBY SUPPLY CURRENT AS A FUNCTION OF SET CURRENT



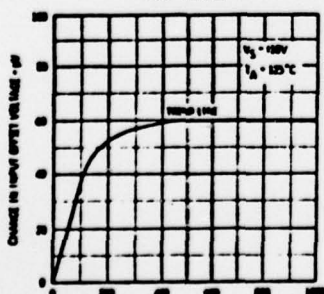
THERMAL RESPONSE OF INPUT OFFSET VOLTAGE TO STEP CHANGE OF CASE TEMPERATURE



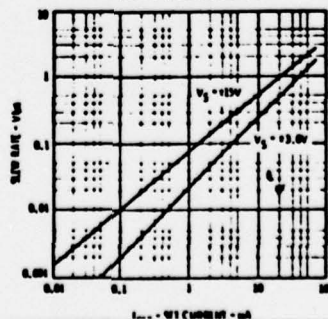
STABILIZATION TIME OF INPUT OFFSET VOLTAGE FROM POWER ON



INPUT OFFSET VOLTAGE DRIFT AS A FUNCTION OF TIME



SLEW RATE AS A FUNCTION OF SET CURRENT



VOLTAGE FOLLOWER TRANSIENT RESPONSE (UNITY GAIN)

